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TABLE OF CONTENTS

Development of AlAsSb as a Barrier Material for Ultra-thin-channel InGaAs nMOSFETs	1
<i>C. Huang, J. Law, H. Lu, M. Rodwell, A. Gossard</i>	
High Integrity SiO₂/Al₂O₃ Gate Stack for Normally-off GaN MOSFET	7
<i>H. Kambayashi, T. Nomura, H. Ueda, K. Harada, Y. Morozumi, K. Hasebe, A. Teramoto, S. Sugawa, T. Ohmi</i>	
Pulsed DC Magnetron Sputtered Rutile TiO₂ Films for Next Generation DRAM Capacitors	13
<i>M. Jithin, L. Kolla, N. Bhat, S. Mohan, Y. Morozumi, S. Kaushal</i>	
High-Performance MIM Capacitors based on TiO₂/ZrO₂/TiO₂ and AlO-doped TiO₂/ZrO₂/TiO₂ Dielectric Stacks for DRAM Applications.....	20
<i>R. Padmanabhan, N. Bhat, S. Mohan, Y. Morozumi, S. Kaushal</i>	
Analysis of Leakage Currents through PLD Grown Ultrathin a-LaGdO₃ Based High-k Metal Gate Devices	29
<i>S. Pavunny, P. Misra, R. Thomas, A. Kumar, J. Scott, R. Katiyar</i>	
Improved Nitridation of GeO₂ Interfacial layer for Ge Gate Stack Technology.....	36
<i>P. Bhatt, K. Chaudhuri, P. Maharaja, A. Nainani, M. Abraham, M. Subramaniam, U. Ganguly, S. Lodha</i>	
Kinetics of Frenkel Defect Formation in TiO₂ from First Principles	42
<i>S. Barabash, C. Chen, D. Pramanik, B. Magyari-Kope, Y. Nishi</i>	
Author Index	